## N-Channel 30-V (D-S) MOSFET

### **Key Features:**

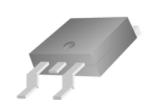
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

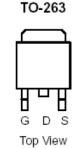
| <b>Typical Applications:</b> |
|------------------------------|
|------------------------------|

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY     |                       |                 |  |  |
|---------------------|-----------------------|-----------------|--|--|
| V <sub>DS</sub> (V) | I⊳(A)                 |                 |  |  |
| 30                  | $3.8 @ V_{GS} = 10V$  | 90 <sup>a</sup> |  |  |
|                     | $4.6 @ V_{GS} = 4.5V$ | 90              |  |  |







| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED) |                      |                   |            |    |  |  |  |
|---|----------------------|-------------------|------------|----|--|--|--|
| Parameter   | Symbol               | Limit             | Units      |    |  |  |  |
| Drain-Source Voltage  | $V_{DS}$             | 30                | V          |    |  |  |  |
| Gate-Source Voltage   |                      | $V_{GS}$          | ±20        | V  |  |  |  |
| Continuous Drain Current a  | T <sub>C</sub> =25°C | I <sub>D</sub>    | 90         | Α  |  |  |  |
| Pulsed Drain Current <sup>b</sup>                                       |                      | I <sub>DM</sub>   | 360        | Α  |  |  |  |
| Continuous Source Current (Diode Conduction) a                          | T <sub>C</sub> =25°C | I <sub>S</sub>    | 90         | Α  |  |  |  |
| Power Dissipation   | T <sub>C</sub> =25°C | $P_{D}$           | 300        | W  |  |  |  |
| Operating Junction and Storage Temperature Range                        |                      | $T_J$ , $T_{stg}$ | -55 to 175 | °C |  |  |  |

| THERMAL RESISTANCE RATINGS    |                 |         |       |
|-------------------------------|-----------------|---------|-------|
| Parameter                     | Symbol          | Maximum | Units |
| Maximum Junction-to-Ambient ° | $R_{\theta JA}$ | 62.5    | °C/W  |
| Maximum Junction-to-Case      | $R_{\theta JC}$ | 1       | C/VV  |

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#### Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board

### **Electrical Characteristics**

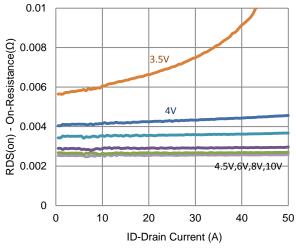
| Parameter                               | Symbol               | Test Conditions   | Min | Тур  | Max  | Unit  |  |  |
|---|----------------------|---|-----|------|------|-------|--|--|
| Static                                  |                      |   |     |      |      |       |  |  |
| Gate-Source Threshold Voltage           | $V_{GS(th)}$         | $V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$                                | 1   |      |      | V     |  |  |
| Gate-Body Leakage                       | $I_{GSS}$            | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                         |     |      | ±100 | nA    |  |  |
| Zero Gate Voltage Drain Current         | 1                    | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$                             |     |      | 1 uA |       |  |  |
| Zero Gate Voltage Drain Current         | I <sub>DSS</sub>     | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ |     |      | 25   | uA    |  |  |
| On-State Drain Current <sup>a</sup>     | I <sub>D(on)</sub>   | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$                             | 110 |      |      | Α     |  |  |
|   | r                    | $V_{GS} = 10 \text{ V}, I_D = 45 \text{ A}$                               |     |      | 3.8  | mΩ    |  |  |
| Drain-Source On-Resistance <sup>a</sup> | r <sub>DS(on)</sub>  | $V_{GS} = 4.5 \text{ V}, I_D = 44 \text{ A}$                              |     |      | 4.6  | 11122 |  |  |
| Forward Transconductance a              | $g_{fs}$             | $V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$                             |     | 25   |      | S     |  |  |
| Diode Forward Voltage <sup>a</sup>      | $V_{SD}$             | I <sub>S</sub> = 45 A, V <sub>GS</sub> = 0 V                              |     | 0.85 |      | V     |  |  |
|   | Dynamic <sup>b</sup> |   |     |      |      |       |  |  |
| Total Gate Charge                       | $Q_g$                | $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$                          |     | 67   |      |       |  |  |
| Gate-Source Charge                      | $Q_{gs}$             | $V_{DS} = 13 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 20 \text{ A}$   |     | 23   |      | nC    |  |  |
| Gate-Drain Charge                       | $Q_gd$               | 1D - 20 A   |     | 35   |      |       |  |  |
| Turn-On Delay Time                      | t <sub>d(on)</sub>   | $V_{DS} = 15 \text{ V}, R_{L} = 0.8 \Omega,$                              |     | 21   |      |       |  |  |
| Rise Time                               | t <sub>r</sub>       | $V_{DS} = 15 \text{ V}, R_L - 0.8 \Omega,$ $I_D = 20 \text{ A},$          |     | 46   |      | ns    |  |  |
| Turn-Off Delay Time                     | $t_{d(off)}$         | $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$                              |     | 164  |      |       |  |  |
| Fall Time                               | t <sub>f</sub>       | VGEN = 10 V, NGEN = 0 12  |     | 83   |      |       |  |  |
| Input Capacitance                       | C <sub>iss</sub>     |   |     | 7650 |      |       |  |  |
| Output Capacitance                      | C <sub>oss</sub>     | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$          |     | 1100 |      | pF    |  |  |
| Reverse Transfer Capacitance            | $C_{rss}$            | 1 1   |     | 1020 |      |       |  |  |

#### Notes

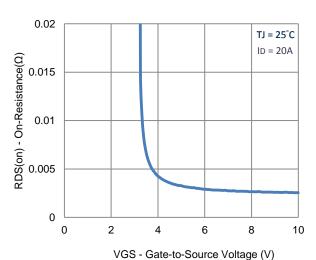
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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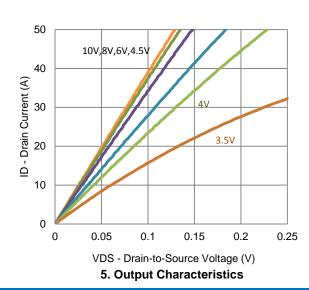
### **Typical Electrical Characteristics**

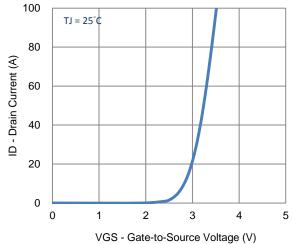


#### 1. On-Resistance vs. Drain Current

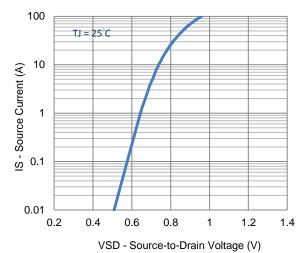


3. On-Resistance vs. Gate-to-Source Voltage

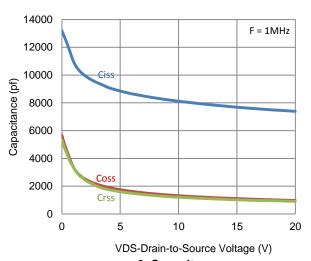




2. Transfer Characteristics

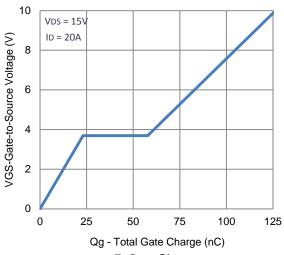


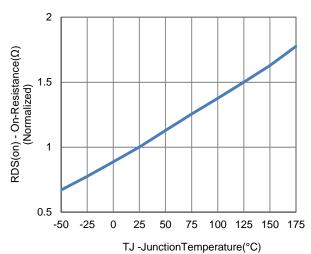
4. Drain-to-Source Forward Voltage



6. Capacitance

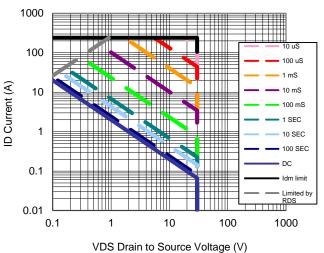
### **Typical Electrical Characteristics**

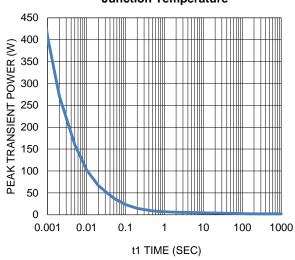






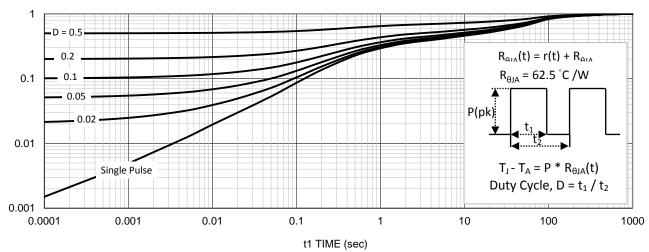
8. Normalized On-Resistance Vs Junction Temperature





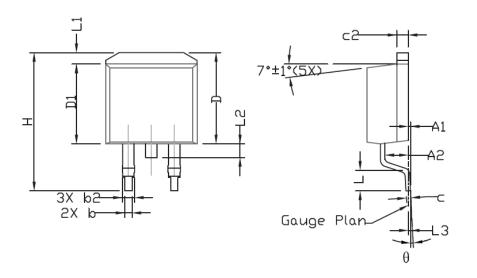
9. Safe Operating Area

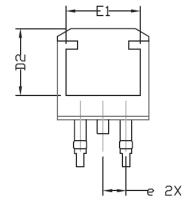
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# **Package Information**





| CVMDEI | DIMENS:  | IONAL F | REQMTS | INCH  | ES REG    | 2TM   |  |
|--------|----------|---------|--------|-------|-----------|-------|--|
| SYMBOL | MIN      | NDM     | MAX    | MIN   | NDM       | MAX   |  |
| A      | 4,30     | 4.57    | 4,72   | 0.169 | 0.180     | 0.186 |  |
| A1     | 0        |         | 0,25   | 0     |           | 0.010 |  |
| A2     | 2,47     | 2.57    | 2,67   | 0.097 | 0.101     | 0.105 |  |
| b      | 0.69     | 0,813   | 0.94   | 0.027 | 0.032     | 0.037 |  |
| b2     | 1,17     | 1,27    | 1,45   | 0.046 | 0.050     | 0.057 |  |
| C      | 0.48     | 0,50    | 0.60   | 0.019 | 0.020     | 0.024 |  |
| c2     | 1.17     | 1.27    | 1.37   | 0.046 | 0.050     | 0,054 |  |
| D      | 9,80     | 10.05   | 10,30  | 0.386 | 0.396     | 0.406 |  |
| D1     | 8,64     | 8.78    | 9,65   | 0.340 | 0,346     | 0,380 |  |
| D2     | 7.12     | 7.37    | 7,62   | 0.280 | 0,290     | 0,300 |  |
| E      | 9,70     | 10.15   | 10.54  | 0,382 | 0.400     | 0.415 |  |
| E1     | 8,00     | 8,20    | 8,40   | 0.315 | 0,323     | 0.331 |  |
| е      | 2.54 BSC |         |        | 0.    | 0.100 BSC |       |  |
| Н      | 14,99    | 15.24   | 15,49  | 0.590 | 0.600     | 0.610 |  |
| L      | 1,78     | 2.29    | 2.79   | 0.070 | 0.090     | 0.110 |  |
| L1     | 1,02     | 1.27    | 1.52   | 0.040 | 0.050     | 0,060 |  |
| L2     |          |         | 1.75   |       |           | 0.069 |  |
| L3     |          | 0,254   |        |       | 0.010     |       |  |
| θ      | 0°       |         | 8*     | 0°    |           | 8*    |  |